



# Solid State Devices, Inc.

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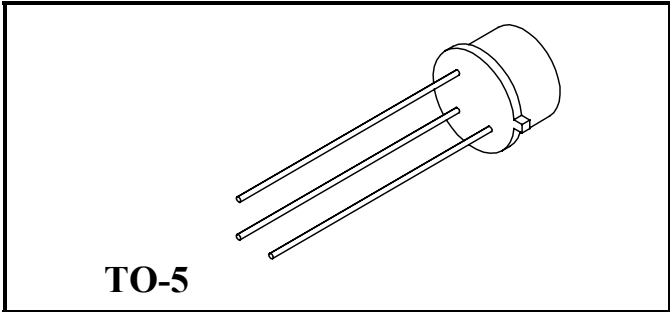
**SSR1008/5**  
**SSR1009/5**  
**SSR1010/5**

**10 AMP**  
**80 – 100 VOLTS**  
**SCHOTTKY RECTIFIER**

## Designer's Data Sheet

### FEATURES:

- Extremely Low Forward Voltage Drop
- Low Reverse Leakage
- Hermetically Sealed Package
- Guard Ring for Overvoltage Protection
- Eutectic Die Attach
- 175°C Operating Junction Temperature
- TX, TXV, or Space Level Screening Available



## MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage and DC Blocking Voltage	$V_{RRM}$	80	Volts
SSR1008/5	$V_{RWM}$	90	
SSR1009/5	$V_R$	100	
SSR1010/5			
Average Rectified Output Current <sup>1/</sup> (Resistive Load, 60Hz, Sine Wave, TA=25°C)	$I_O$	10	Amps
Peak Surge Current <sup>1/</sup> (8.3 ms Pulse, Half Sine Wave, superimposed on $I_O$ , allow junction to reach equilibrium between pulses, TA=25°C)	$I_{FSM}$	150	Amps
Operating and Storage Temperature	$T_{OP}$ & $T_{STG}$	-65 to +175	°C
Maximum Thermal Resistance <sup>1/</sup> Junction to Case	$R_{\theta JC}$	7.0	°C/W

Notes: <sup>1/</sup> For optimal performance, connect leads 1 & 2 together (Anode).



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**ELECTRICAL CHARACTERISTICS**

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
<b>Instantaneous Forward Voltage Drop <sup>2/</sup></b> (I <sub>F</sub> = 1 Adc, T <sub>A</sub> = 25°C, 300 - 500µs Pulse) (I <sub>F</sub> = 5 Adc, T <sub>A</sub> = 25°C, 300 - 500µs Pulse) (I <sub>F</sub> = 10 Adc, T <sub>A</sub> = 25°C, 300 - 500µs Pulse)	V <sub>F1</sub> V <sub>F2</sub> V <sub>F3</sub>	0.56 0.73 0.85	Vdc
<b>Instantaneous Forward Voltage Drop</b> (I <sub>F</sub> = 5 Adc, T <sub>A</sub> = -55°C, 300 - 500µs Pulse)	V <sub>F4</sub>	0.82	Vdc
<b>Reverse Leakage Current</b> (Rated V <sub>R</sub> , T <sub>A</sub> = 25°C, 300µs Pulse Minimum)	I <sub>R1</sub>	100	µA
<b>Reverse Leakage Current</b> (Rated V <sub>R</sub> , T <sub>A</sub> = 100°C, 300µs Pulse Minimum)	I <sub>R2</sub>	5	mA
<b>Junction Capacitance</b> (V <sub>R</sub> = 10 Vdc, T <sub>A</sub> = 25°C, f = 1 MHz)	C <sub>J</sub>	400	pF

NOTES:

<sup>2/</sup> V<sub>F</sub> as measured between pins 1 and 2 in common, within .100" from the case, and pin 3 directly at the case.

